	Hits	Search Text	DBs	Tim Stamp
1	120553	(second! or another or additional) near4 channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:20
2	141360	(FET or (field adj effect adj transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:20
3	780776	gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:20
4	17016	((second! or another or additional) near4 channel) same gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:20
5	5837	(((second! or another or additional) near4 channel) same gate) and ((FET or (field adj effect adj transistor)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:20
6	259	(((second! or another or additional) near4 channel) same gate) same sidewalls	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:20
7	101	((((second! or another or additional) near4 channel) same gate) same sidewalls) and ((FET or (field adj effect adj transistor)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:20
8	948	channels near2 (silicon or Si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:20
9	6985	(vertical adj channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:20
10	0	((vertical adj channel)) near8 (thin adj gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:20
11	105	epitaxial adj channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:21
12	27270	(etch or remov$6) near4 channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:21
13	1989	((etch or remov$6) near4 channel) and (second! adj channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:21

	Hits	Search Text	DBs	Time Stamp
14	28320	second adj channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:21
15	73	(((((second! or another or additional) near4 channel) same gate) same sidewalls) and ((FET or (field adj effect adj transistor)))) and @ad<20001018	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:21
16	11	((((((second! or another or additional) near4 channel) same gate) same sidewalls) and ((FET or (field adj effect adj transistor)))) and @ad<20001018) and (SOI or (silicon adj on adj insulator))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:21
17	3	(channels near2 (silicon or Si)) near8 sidewall	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:21
18	9	(channels near2 (silicon or Si)) same sidewall	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:21
19	105	epitaxial adj channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:21
20	5	((vertical adj channel)) same (thin adj gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:21
21	11	((((((second! or another or additional) near4 channel) same gate) same sidewalls) and ((FET or (field adj effect adj transistor)))) and @ad<20001018) and (SOI or (silicon adj on adj insulator))) and ((FET or (field adj effect adj transistor)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/03 16:21